



# STB7NK80Z, STB7NK80Z-1 STP7NK80ZFP, STP7NK80Z

N-channel 800 V, 1.5  $\Omega$ , 5.2 A, TO-220, TO-220FP, D<sup>2</sup>PAK, I<sup>2</sup>PAK  
Zener-protected SuperMESH™ Power MOSFET

## Features

Type	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub>	I <sub>D</sub>
STP7NK80Z	800V	< 1.8 $\Omega$	5.2A
STP7NK80ZFP	800V	< 1.8 $\Omega$	5.2A
STB7NK80Z	800V	< 1.8 $\Omega$	5.2A
STB7NK80Z-1	800V	< 1.8 $\Omega$	5.2A

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

## Applications

- Switching application

## Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage Power MOSFETs including revolutionary MDmesh™ products.

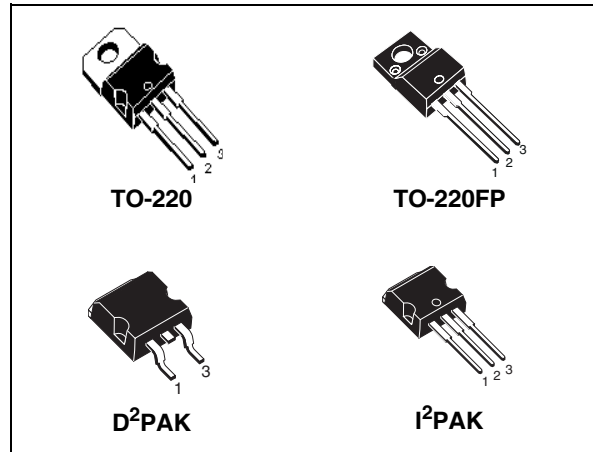


Figure 1. Internal schematic diagram

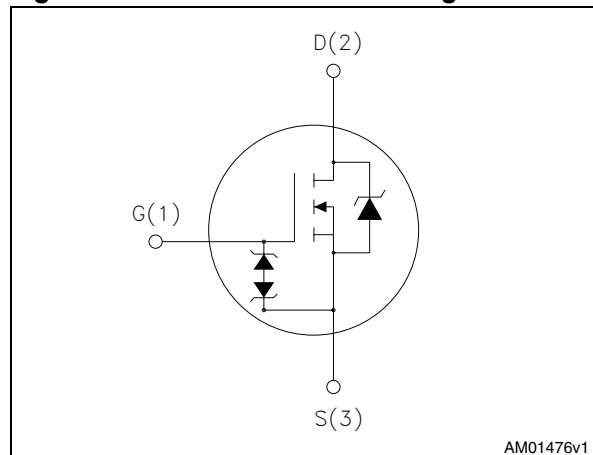


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB7NK80ZT4	B7NK80Z	D <sup>2</sup> PAK	Tape e reel
STB7NK80Z-1	B7NK80Z	I <sup>2</sup> PAK	Tube
STP7NK80Z	P7NK80Z	TO-220	
STP7NK80ZFP	P7NK80ZFP	TO-220FP	

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value				Unit
		TO-220	D <sup>2</sup> PAK	I <sup>2</sup> PAK	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	800				V
V <sub>GS</sub>	Gate- source voltage	± 30				V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	5.2		5.2 <sup>(1)</sup>		A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	3.3		3.3 <sup>(1)</sup>		A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	20.8		20.8 <sup>(1)</sup>		A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25°C	125		30		W
	Derating factor	1		0.24		W/°C
V <sub>ESD(G-S)</sub>	Gate source ESD (HBM-C=100 pF, R=1.5 kΩ)	4000				V
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	4.5				V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T <sub>C</sub> = 25 °C)				2500	V
T <sub>j</sub> T <sub>stg</sub>	Max operating junction temperature Storage temperature	-55 to 150				°C °C

1. Limited only by maximum temperature allowed

2. Pulse width limited by safe operating area

3. I<sub>SD</sub> ≤ 5.2 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		TO-220	D <sup>2</sup> PAK	I <sup>2</sup> PAK	TO-220FP	
R <sub>thj-case</sub>	Thermal resistance junction-case max	1		4.2		°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	62.5				°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose	300				°C

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by T <sub>j</sub> Max)	5.2	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	210	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	800			V
$I_{DSS}$	Zero gate voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2.6\text{ A}$		1.5	1.8	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$ , $I_D = 2.6\text{ A}$	-	5		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	1138 122 25		$\mu\text{F}$ $\mu\text{F}$ $\mu\text{F}$
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{DS} = 0$ , $V_{DS} = 0\text{ to }640\text{ V}$	-	50		$\mu\text{F}$
$t_{d(on)}$ $t_r$ $t_{r(off)}$ $t_f$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 400\text{ V}$ , $I_D = 2.6\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	20 12 45 20		ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 640\text{ V}$ , $I_D = 5.2\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> )	-	40 7 21	56	nC nC nC
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage rise time Fall time Cross-over time	$V_{DD} = 640\text{ V}$ , $I_D = 5.2\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	12 10 20		ns ns ns

1. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

2.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit		
$I_{SD}$	Source-drain current		-		5.2	A		
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		20.8	A		
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5.2 \text{ A}, V_{GS} = 0$	-		1.6	V		
$t_{rr}$	Reverse recovery time	$I_{SD} = 5.2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 50 \text{ V}, T_J = 150^\circ\text{C}$ (see <a href="#">Figure 22</a> )	-	530		ns		
$Q_{rr}$	Reverse recovery charge						3.31	$\mu\text{C}$
$I_{RRM}$	Reverse recovery current						12.5	A

1. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%
2. Pulse width limited by safe operating area

**Table 8. Gate-source zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}$ (open drain)	30			V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK

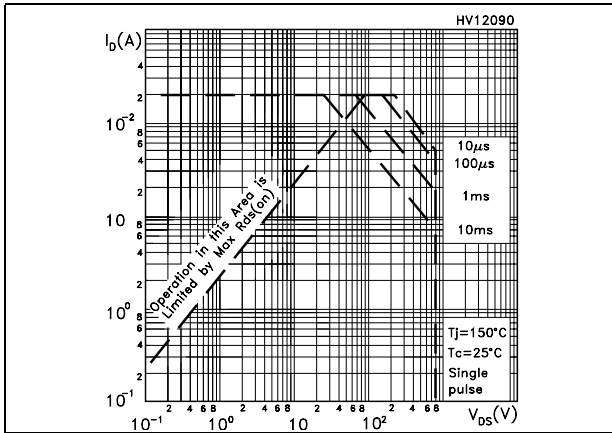


Figure 3. Thermal impedance for TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK

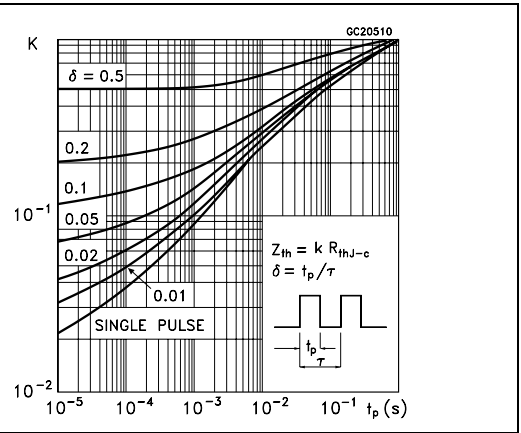


Figure 4. Safe operating area for TO-220FP

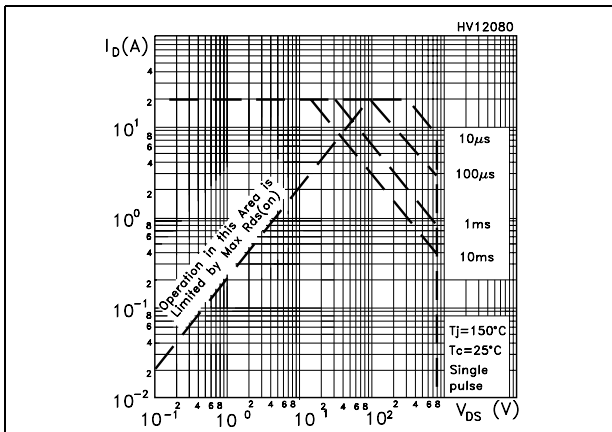


Figure 5. Thermal impedance for TO-220FP

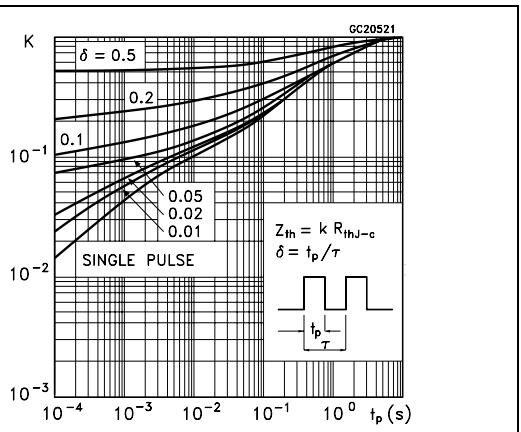


Figure 6. Output characteristics

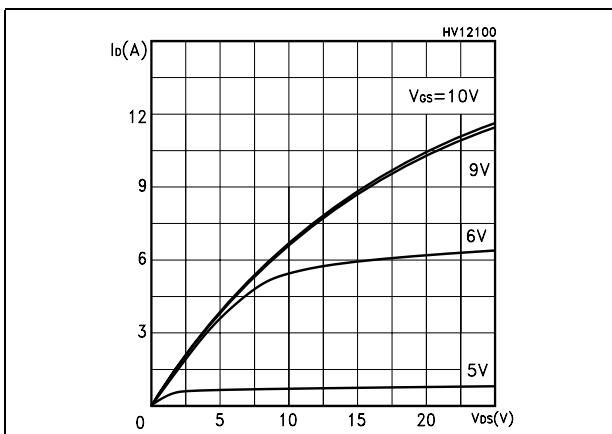


Figure 7. Transfer characteristics

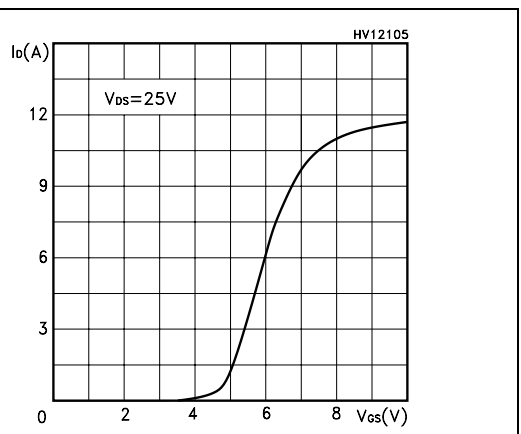


Figure 8. Transconductance

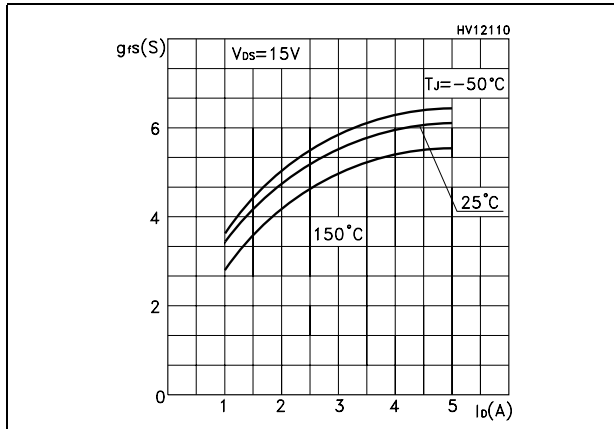


Figure 9. Static drain-source on resistance

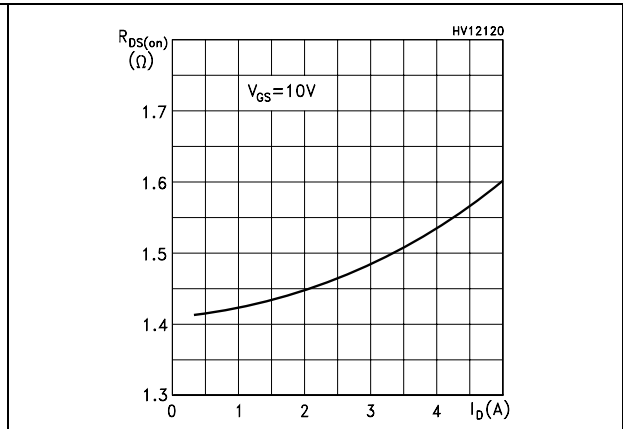


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

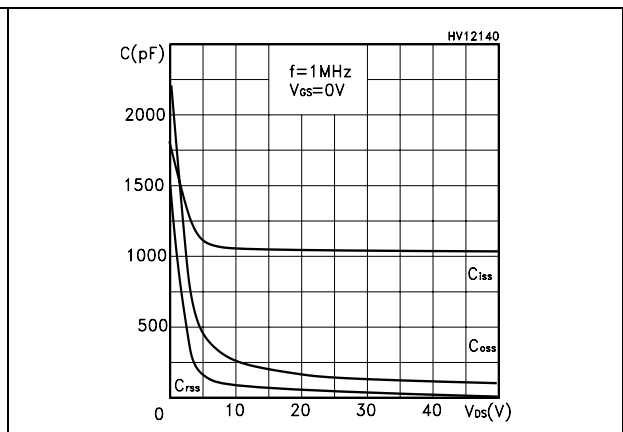
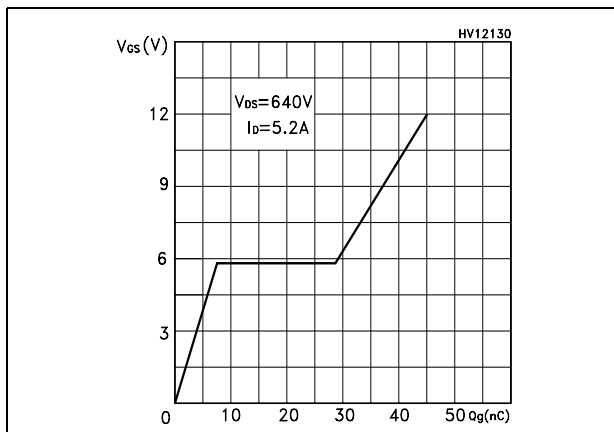


Figure 12. Normalized gate threshold voltage vs temperature

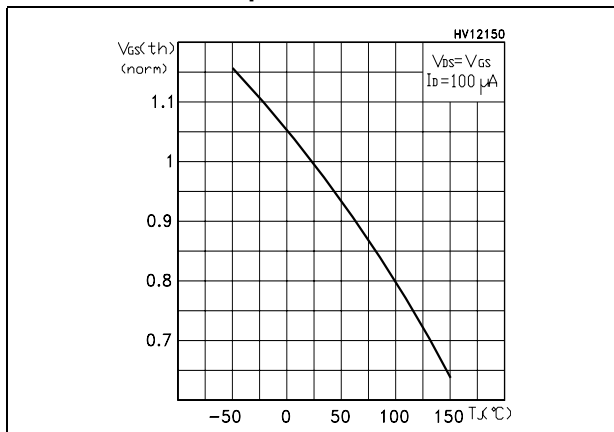


Figure 13. Normalized on resistance vs temperature

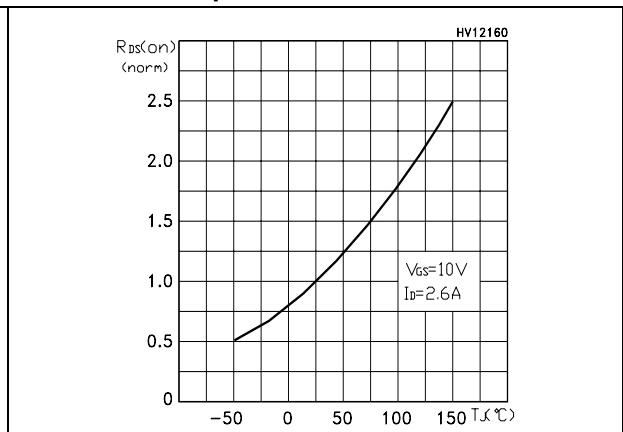


Figure 14. Source-drain diode forward characteristic

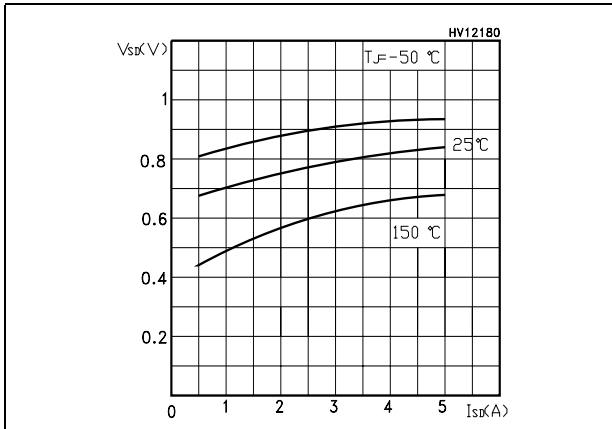


Figure 15. Normalized BVDSS vs temperature

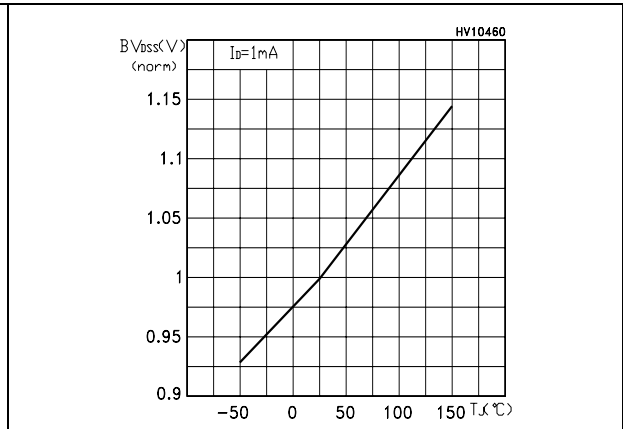
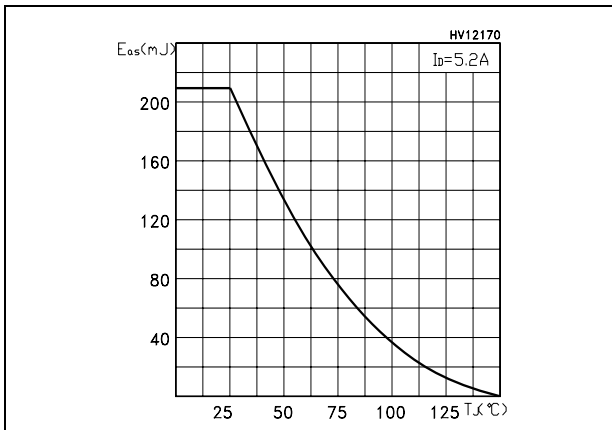


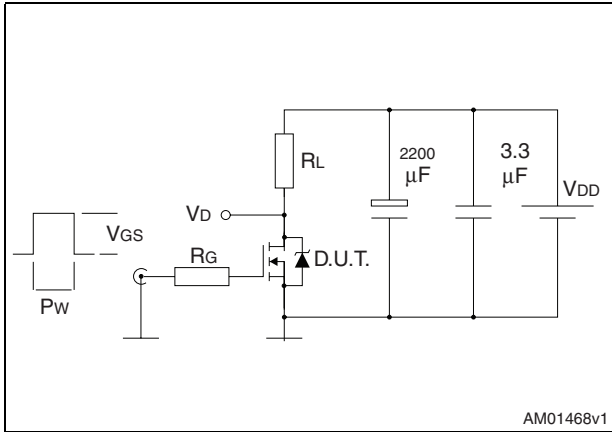
Figure 16. Maximum avalanche energy vs temperature





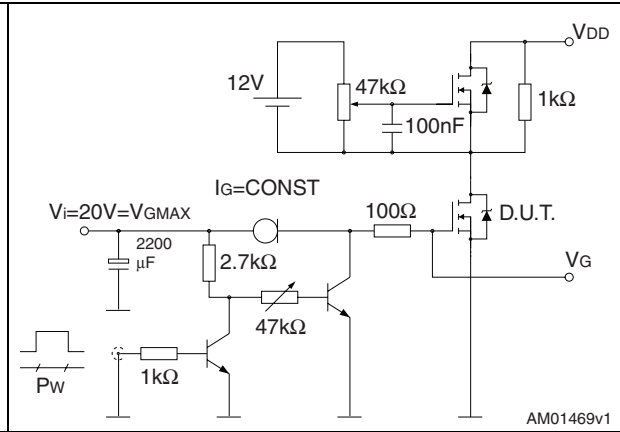
### 3 Test circuits

**Figure 17. Switching times test circuit for resistive load**



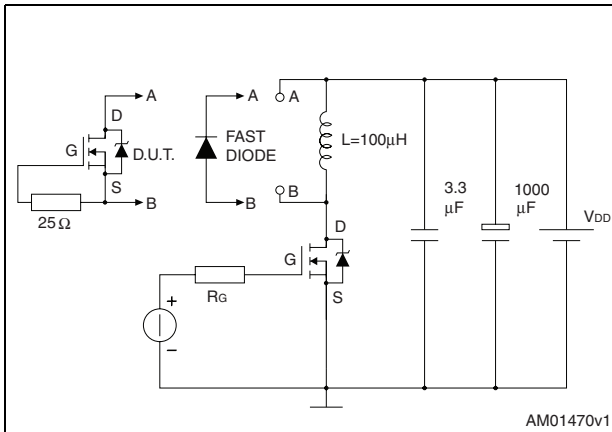
AM01468v1

**Figure 18. Gate charge test circuit**



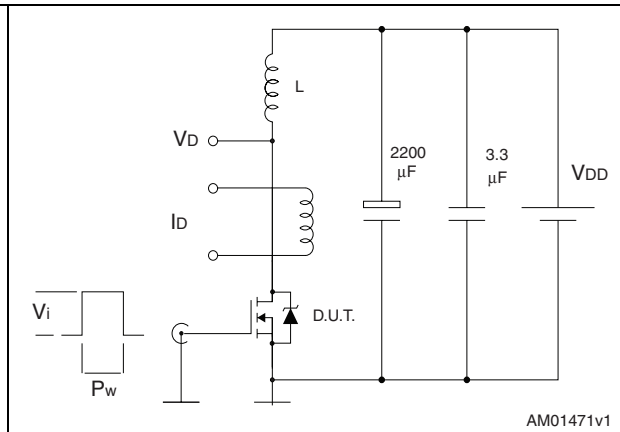
AM01469v1

**Figure 19. Test circuit for inductive load switching and diode recovery times**



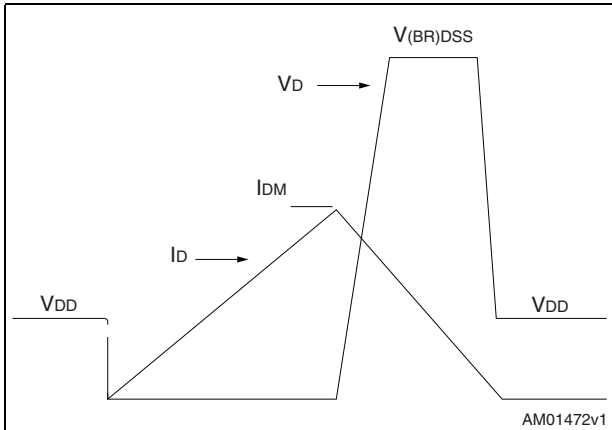
AM01470v1

**Figure 20. Unclamped inductive load test circuit**



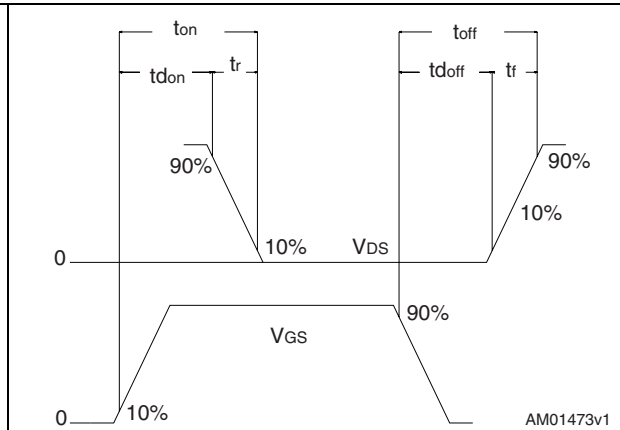
AM01471v1

**Figure 21. Unclamped inductive waveform**



AM01472v1

**Figure 22. Switching time waveform**



AM01473v1

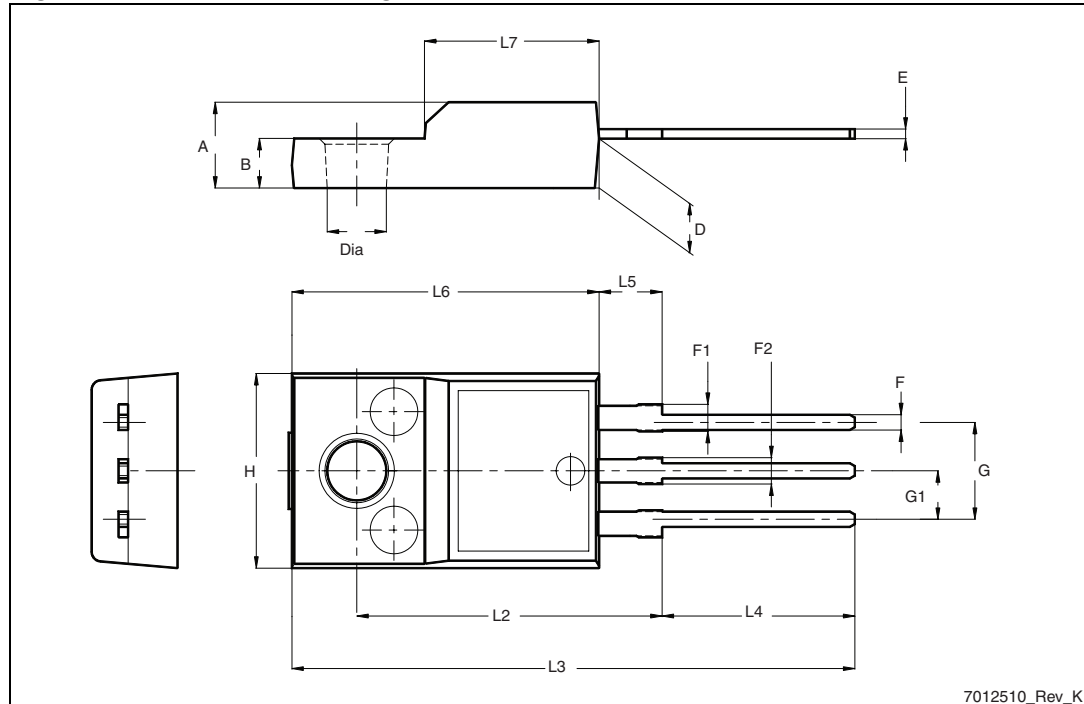
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

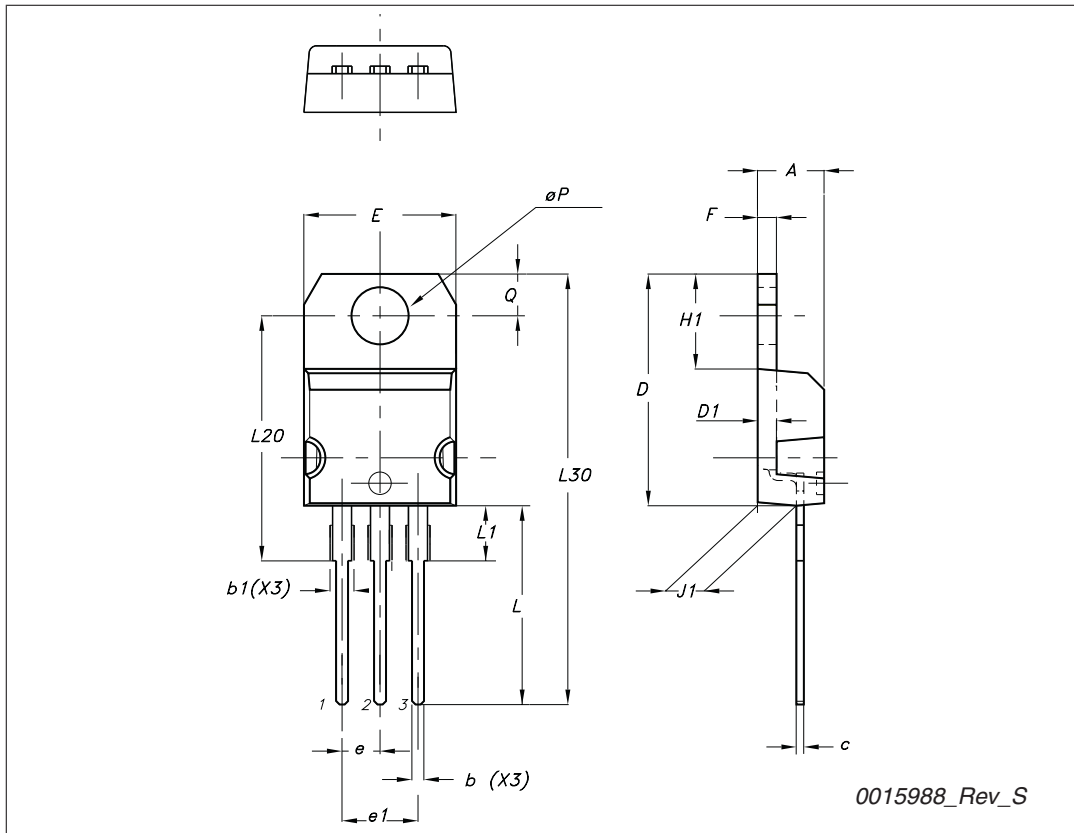
Figure 23. TO-220FP drawing



7012510\_Rev\_K

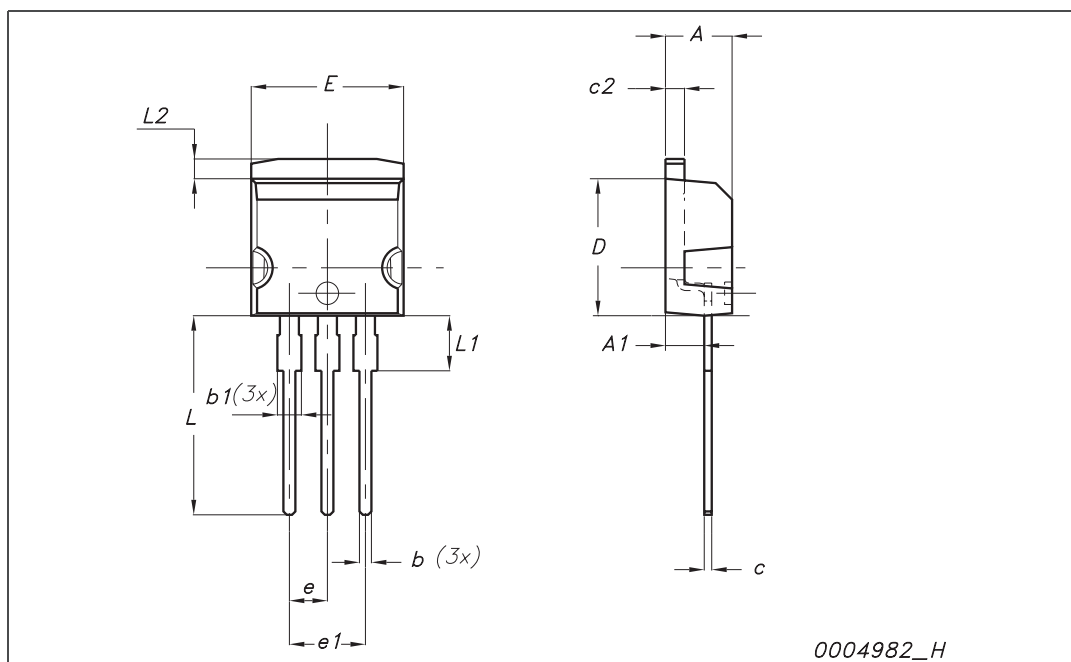
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



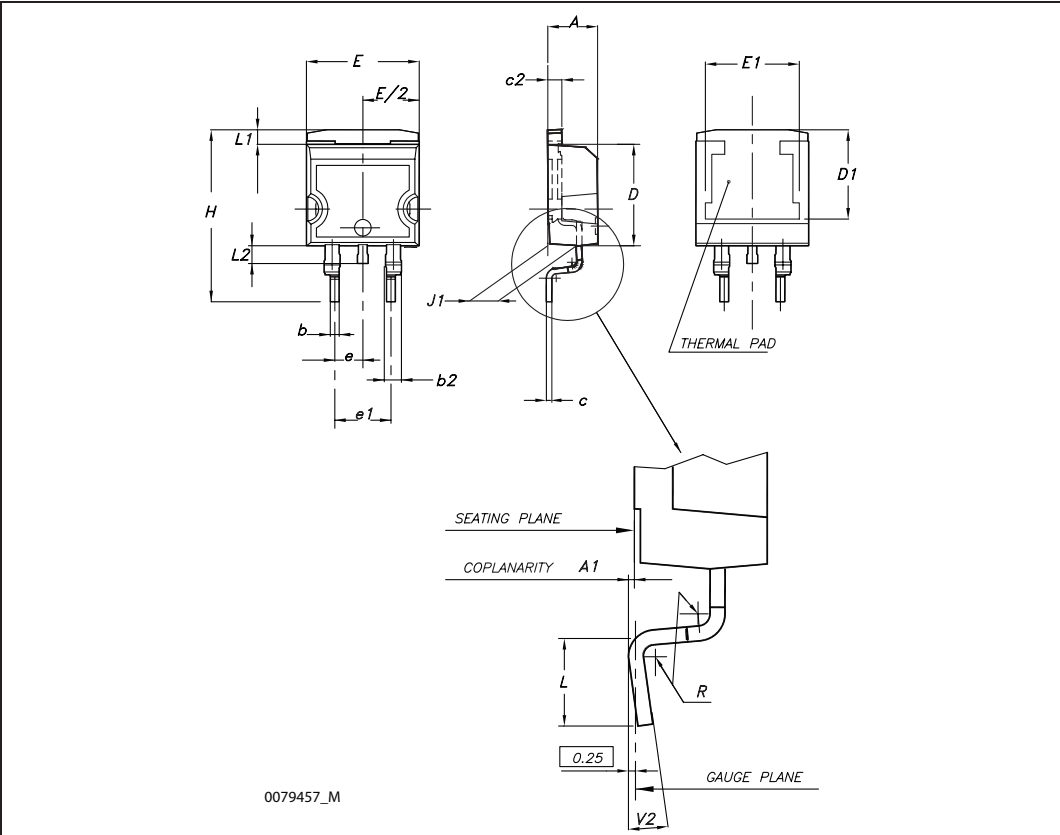
I<sup>2</sup>PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



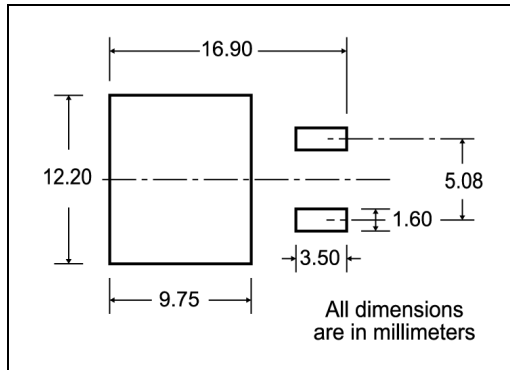
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

\* on sales type

## 6 Revision history

**Table 10. Revision history**

Date	Revision	Changes
09-Sep-2004	3	Complete version
16-Aug-2006	4	New template, no content change
09-Oct-2006	5	Corrected order code
28-Mar-2010	6	Corrected <a href="#">Table 1: Device summary</a>



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